

N-Channel Enhancement Mode MOSFET

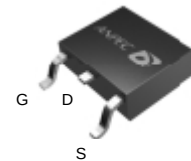
Features

- 30V/40A ,
 $R_{DS(ON)} = 9m\Omega (typ.) @ V_{GS} = 10V$
 $R_{DS(ON)} = 13m\Omega (typ.) @ V_{GS} = 4.5V$
- Super High Dense Cell Design
- Avalanche Rated
- Reliable and Rugged
- Lead Free Available (RoHS Compliant)

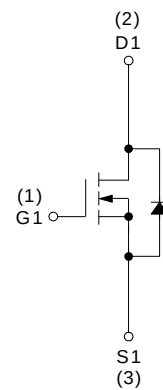
Applications

- Power Management in Desktop Computer or DC/DC Converters

Pin Description



Top View of TO-252



N-Channel MOSFET

Ordering and Marking Information

APM3011N □□-□□□ Lead Free Code Handling Code Temp. Range Package Code	Package Code U : TO-252 Operating Junction Temp. Range C : -55 to 150°C Handling Code TU : Tube TR : Tape & Reel Lead Free Code L : Lead Free Device Blank : Original Device
APM3011N U : 	XXXXX - Date Code

Note: ANPEC lead-free products contain molding compounds/die attach materials and 100% matte in plate termination finish; which are fully compliant with RoHS and compatible with both SnPb and lead-free soldering operations. ANPEC lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J STD-020C for MSL classification at lead-free peak reflow temperature.

ANPEC reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (T _A =25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		30	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	°C
Mounted on Large Heat Sink				
I _{DP}	300μs Pulse Drain Current Tested	T _C =25°C	100	A
		T _C =100°C	65	
I _D	Continuous Drain Current	T _C =25°C	40	A
		T _C =100°C	22	
P _D	Maximum Power Dissipation	T _C =25°C	50	W
		T _C =100°C	20	
R _{θJC}	Thermal Resistance-Junction to Case		2.5	°C/W
Mounted on PCB of 1in ² pad area				
I _{DP}	300μs Pulse Drain Current Tested	T _A =25°C	100	A
		T _A =100°C	65	
I _D	Continuous Drain Current	T _A =25°C	10	A
		T _A =100°C	6	
P _D	Maximum Power Dissipation	T _A =25°C	2.5	W
		T _A =100°C	1	
R _{θJA}	Thermal Resistance-Junction to Ambient		50	°C/W
Mounted on PCB of Minimum Footprint				
I _{DP}	300μs Pulse Drain Current Tested	T _A =25°C	100	A
		T _A =100°C	65	
I _D	Continuous Drain Current	T _A =25°C	7	A
		T _A =100°C	4	
P _D	Maximum Power Dissipation	T _A =25°C	1.5	W
		T _A =100°C	0.5	
R _{θJA}	Thermal Resistance-Junction to Ambient		75	°C/W

Electrical Characteristics (T_A = 25°C unless otherwise noted)

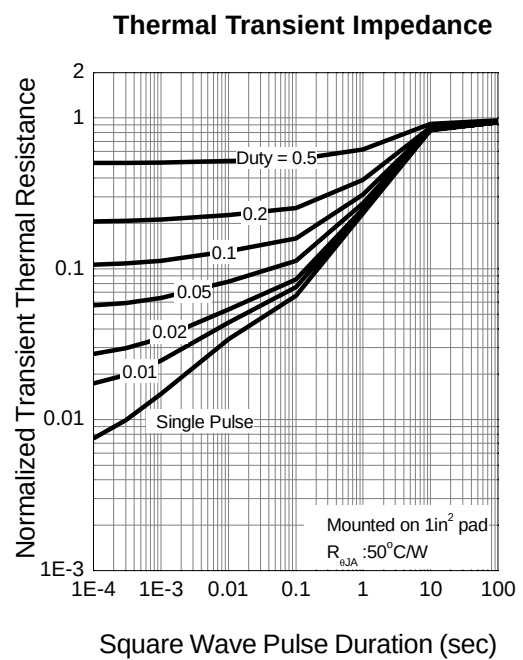
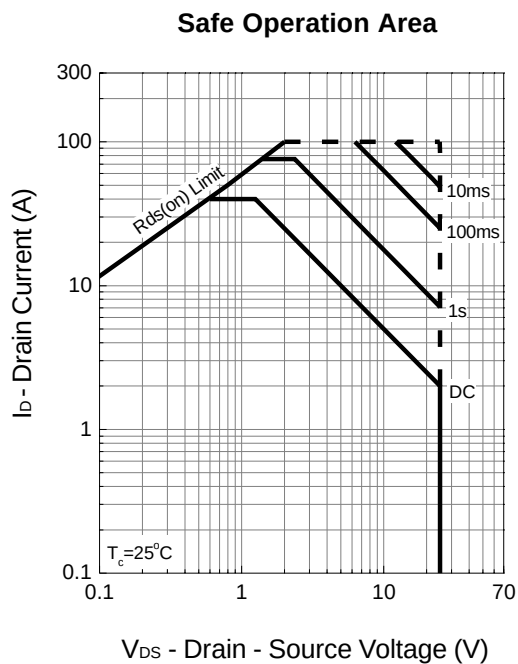
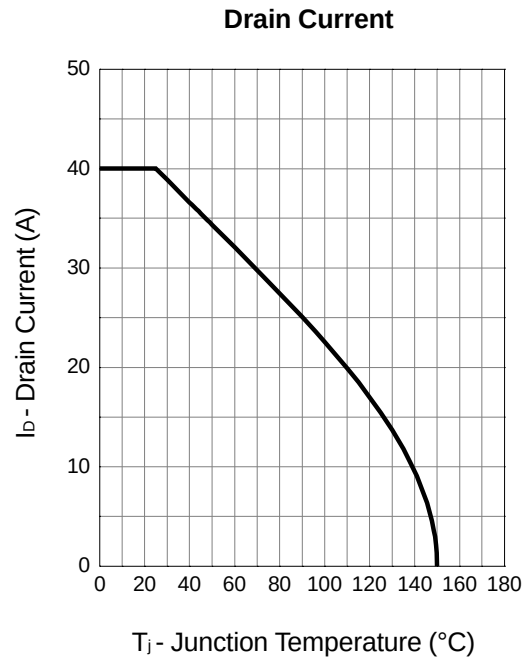
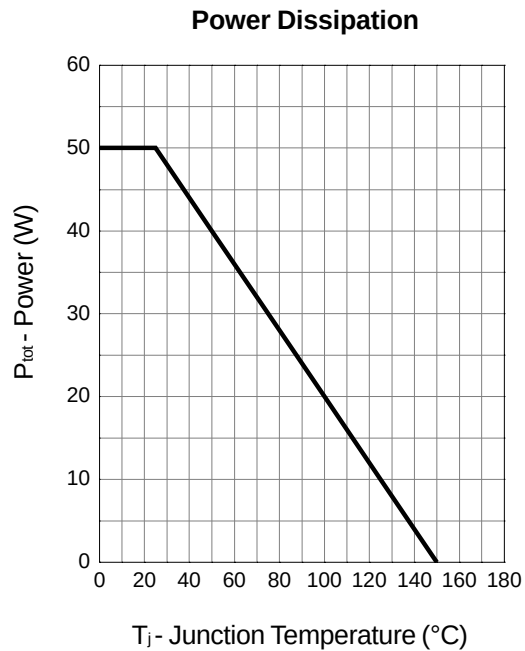
Symbol	Parameter	Test Condition	APM3011NU			Unit
			Min.	Typ.	Max.	
Drain-Source Avalanche Ratings						
E _{AS}	Drain-Source Avalanche Energy	I _D =20A, V _{DD} =20V			100	mJ
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V			1	μA
		T _J =85°C			30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1	1.5	2	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
R _{DS(ON)} ^a	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =20A		9	11	mΩ
		V _{GS} =4.5V, I _{DS} =10A		13	17	
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	I _{SD} =10A , V _{GS} =0V		0.9	1.3	V
I _S ^b	Diode continuous forward current	T _C =25°C			20	A
Dynamic Characteristics ^b						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, Frequency=1.0MHz		1560		pF
C _{oss}	Output Capacitance			345		
C _{rss}	Reverse Transfer Capacitance			245		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =15V, R _L =15Ω, I _{DS} =1A, V _{GEN} =4.5V, R _G =6Ω		10	20	ns
T _r	Turn-on Rise Time			15	25	
t _{d(OFF)}	Turn-off Delay Time			35	50	
T _f	Turn-off Fall Time			15	20	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =4.5V, I _{DS} =20A		17.8	24	nC
Q _{gs}	Gate-Source Charge			4.6		
Q _{gd}	Gate-Drain Charge			10		

Notes:

a : Pulse test ; pulse width ≤300μs, duty cycle ≤ 2%.

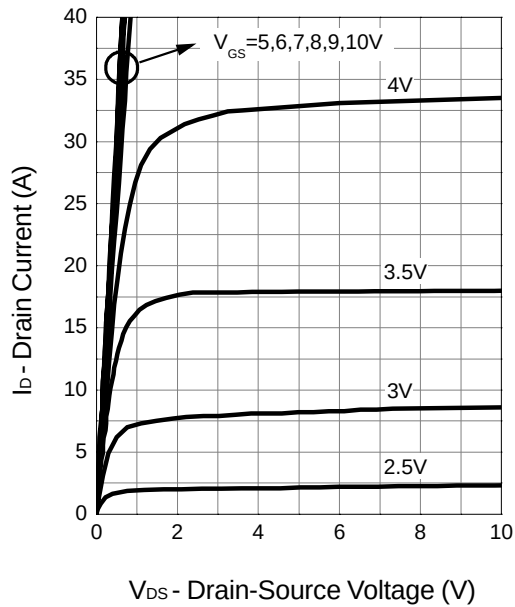
b : Guaranteed by design, not subject to production testing.

Typical Characteristics

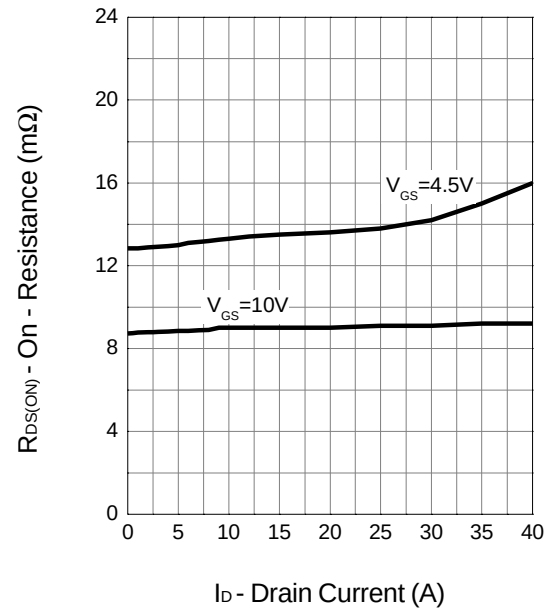


Typical Characteristics (Cont.)

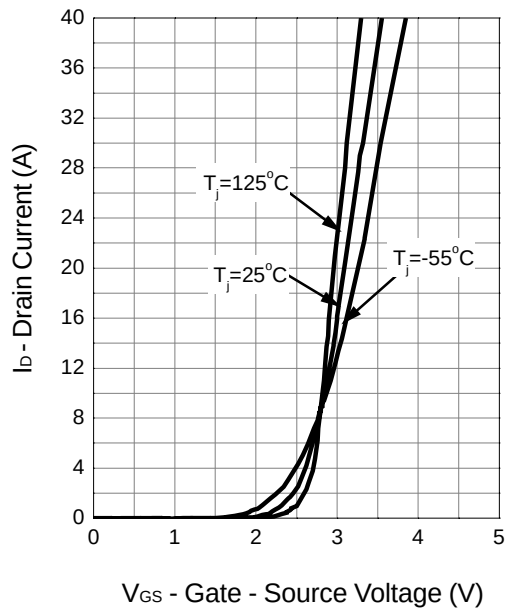
Output Characteristics



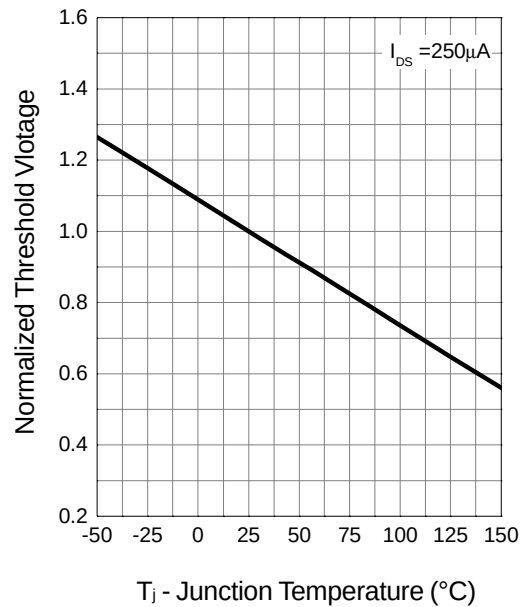
Drain-Source On Resistance



Transfer Characteristics

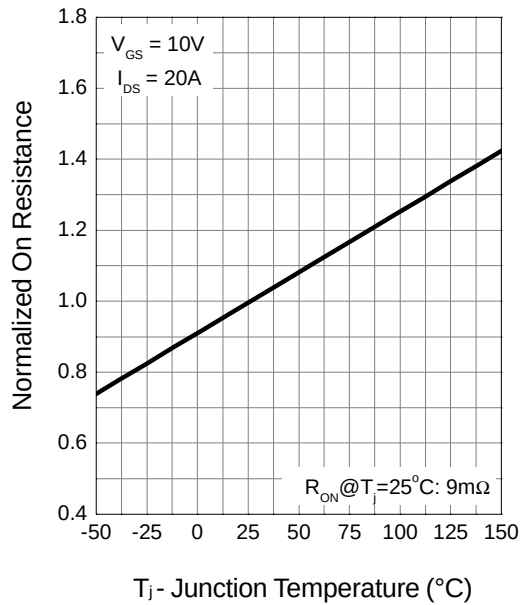


Gate Threshold Voltage

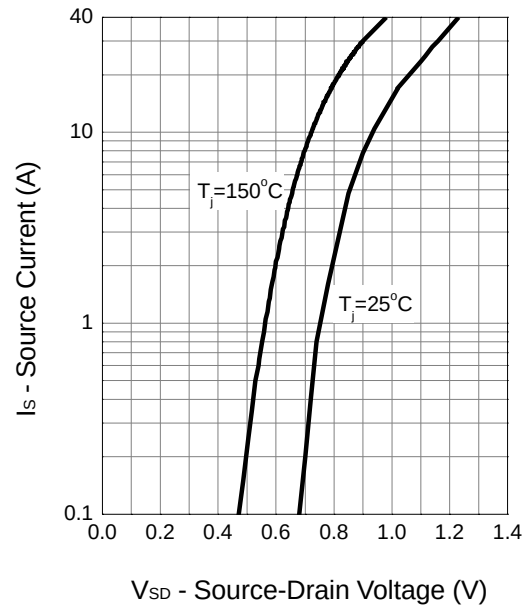


Typical Characteristics (Cont.)

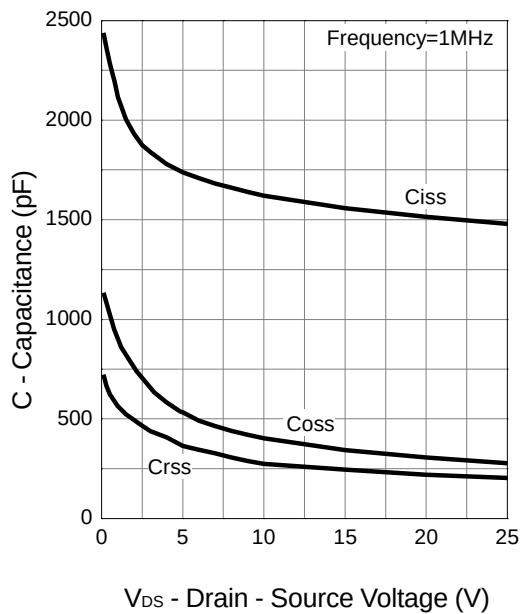
Drain-Source On Resistance



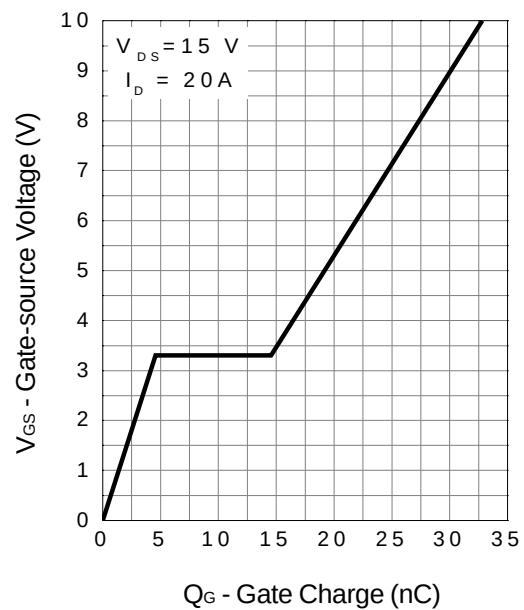
Source-Drain Diode Forward



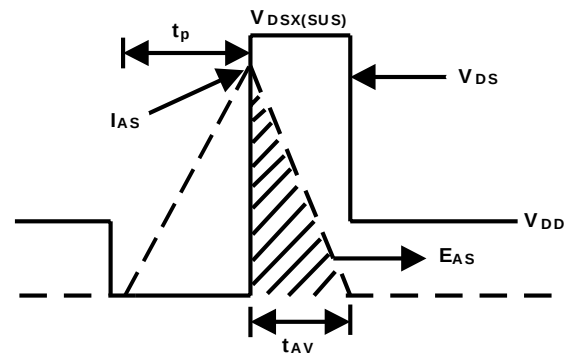
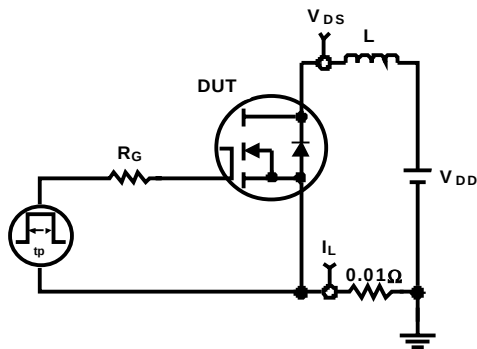
Capacitance



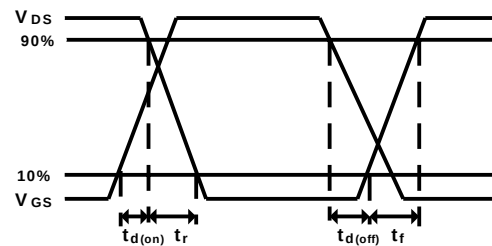
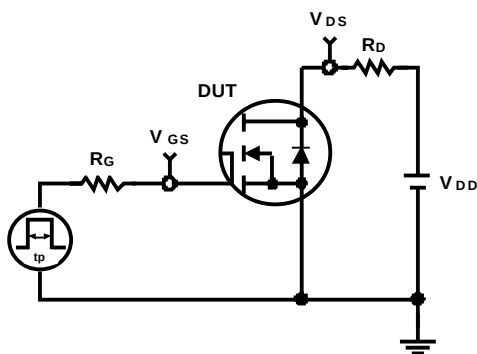
Gate Charge



Avalanche Test Circuit and Waveforms

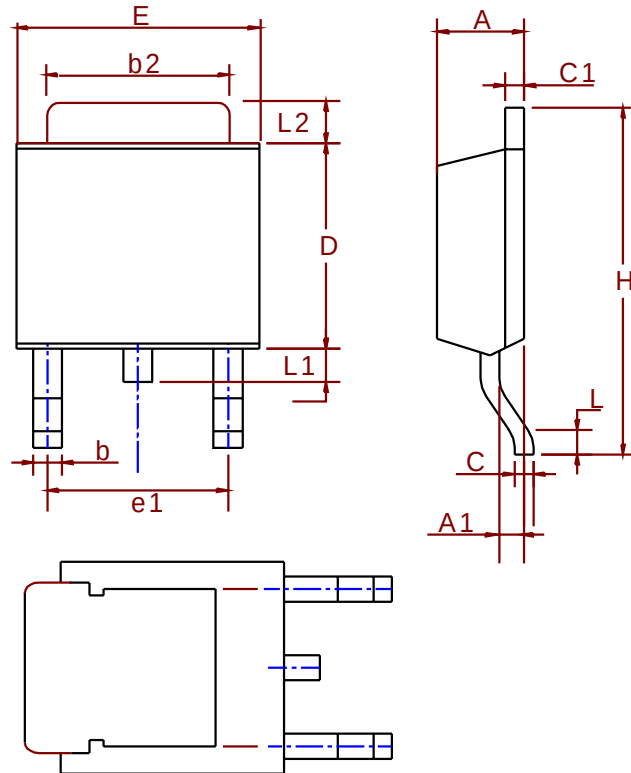


Switching Time Test Circuit and Waveforms



Packaging Information

TO-252(Reference JEDEC Registration TO-252)

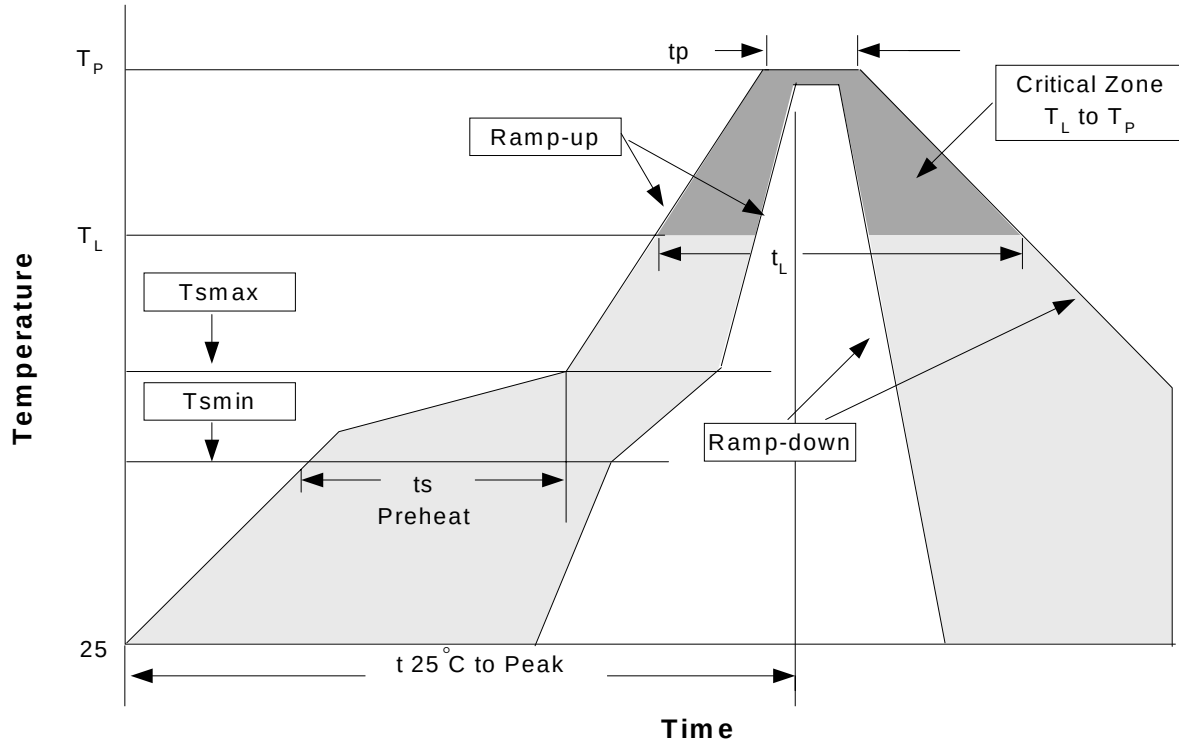


Dim	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.18	2.39	0.086	0.094
A1	0.89	1.27	0.035	0.050
b	0.508	0.89	0.020	0.035
b2	5.207	5.461	0.205	0.215
C	0.46	0.58	0.018	0.023
C1	0.46	0.58	0.018	0.023
D	5.334	6.22	0.210	0.245
E	6.35	6.73	0.250	0.265
e1	3.96	5.18	0.156	0.204
H	9.398	10.41	0.370	0.410
L	0.51		0.020	
L1	0.64	1.02	0.025	0.040
L2	0.89	2.032	0.035	0.080

Physical Specifications

Terminal Material	Solder-Plated Copper (Solder Material : 90/10 or 63/37 SnPb), 100%Sn
Lead Solderability	Meets EIA Specification RSI86-91, ANSI/J-STD-002 Category 3.

Reflow Condition (IR/Convection or VPR Reflow)



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	3°C/second max.	3°C/second max.
Preheat - Temperature Min (T_{smin}) - Temperature Max (T_{smax}) - Time (min to max) (t_s)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: - Temperature (T_L) - Time (t_L)	183°C 60-150 seconds	217°C 60-150 seconds
Peak/Classification Temperature (T_P)	See table 1	See table 2
Time within 5°C of actual Peak Temperature (t_p)	10-30 seconds	20-40 seconds
Ramp-down Rate	6°C/second max.	6°C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

Notes: All temperatures refer to topside of the package .Measured on the body surface.

Classification Reflow Profiles(Cont.)

Table 1. SnPb Eutectic Process – Package Peak Reflow Temperatures

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	240 +0/-5°C	225 +0/-5°C
≥2.5 mm	225 +0/-5°C	225 +0/-5°C

Table 2. Pb-free Process – Package Classification Reflow Temperatures

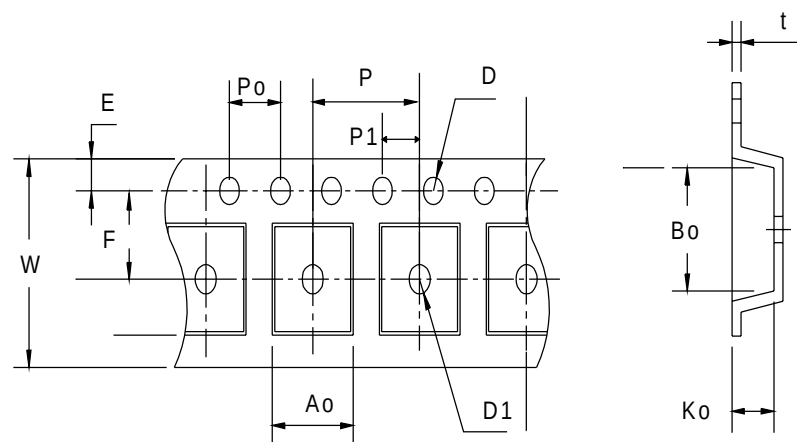
Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 +0°C*	260 +0°C*	260 +0°C*
1.6 mm – 2.5 mm	260 +0°C*	250 +0°C*	245 +0°C*
≥2.5 mm	250 +0°C*	245 +0°C*	245 +0°C*

*Tolerance: The device manufacturer/supplier **shall** assure process compatibility up to and including the stated classification temperature (this means Peak reflow temperature +0°C. For example 260°C+0°C) at the rated MSL level.

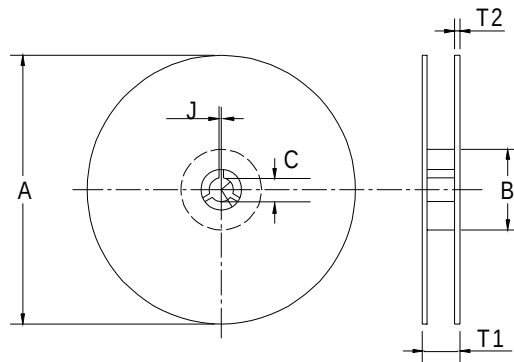
Reliability Test Program

Test item	Method	Description
SOLDERABILITY	MIL-STD-883D-2003	245°C, 5 SEC
HOLT	MIL-STD 883D-1005.7	1000 Hrs Bias @ 125°C
PCT	JESD-22-B, A102	168 Hrs, 100% RH, 121°C
TST	MIL-STD 883D-1011.9	-65°C ~ 150°C, 200 Cycles

Carrier Tape & Reel Dimensions



Carrier Tape & Reel Dimensions(Cont.)



Application	A	B	C	J	T1	T2	W	P	E
TO-252	330 ±3	100 ±2	13 ±0.5	2 ±0.5	16.4 +0.3 -0.2	2.5 ±0.5	16 +0.3 -0.1	8 ±0.1	1.75 ±0.1
	F	D	D1	Po	P1	Ao	Bo	Ko	t
	7.5 ±0.1	1.5 ±0.1	1.5 ±0.25	4.0 ±0.1	2.0 ±0.1	6.8 ±0.1	10.4 ±0.1	2.5 ±0.1	0.3 ±0.05

(mm)

Cover Tape Dimensions

Application	Carrier Width	Cover Tape Width	Devices Per Reel
TO- 252	16	13.3	2500

Customer Service

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